

PMV185XN

30 V, single N-channel Trench MOSFET

3 August 2012

Product data sheet

1. Product profile

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Low R_{DSon}
- Very fast switching
- Trench MOSFET technology

1.3 Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_{amb} = 25\text{ }^{\circ}\text{C}$		-	-	30	V
V_{GS}	gate-source voltage			-12	-	12	V
I_D	drain current	$V_{GS} = 4.5\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; $t \leq 5\text{ s}$	[1]	-	-	1.2	A
Static characteristics							
R_{DSon}	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}$; $I_D = 1.1\text{ A}$; $T_J = 25\text{ }^{\circ}\text{C}$		-	185	250	m Ω

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

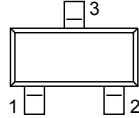
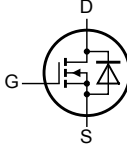


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2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 TO-236AB (SOT23)	 017aaa253
2	S	source		
3	D	drain		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMV185XN	TO-236AB	plastic surface-mounted package; 3 leads	SOT23

4. Marking

Table 4. Marking codes

Type number	Marking code [1]
PMV185XN	EH%

[1] % = placeholder for manufacturing site code

5. Limiting values

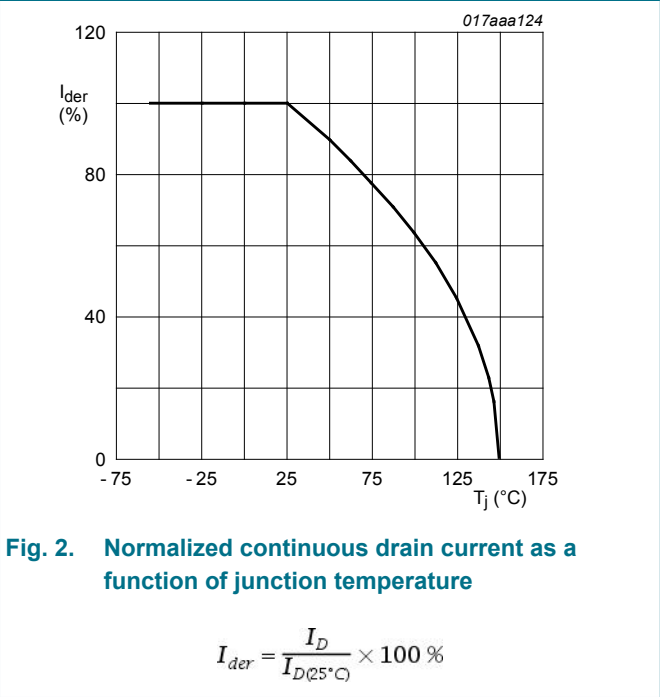
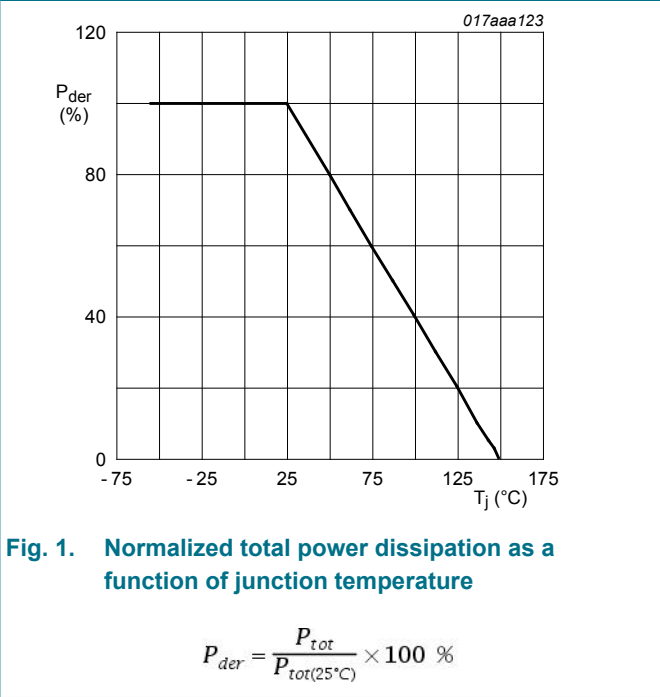
Table 5. Limiting values

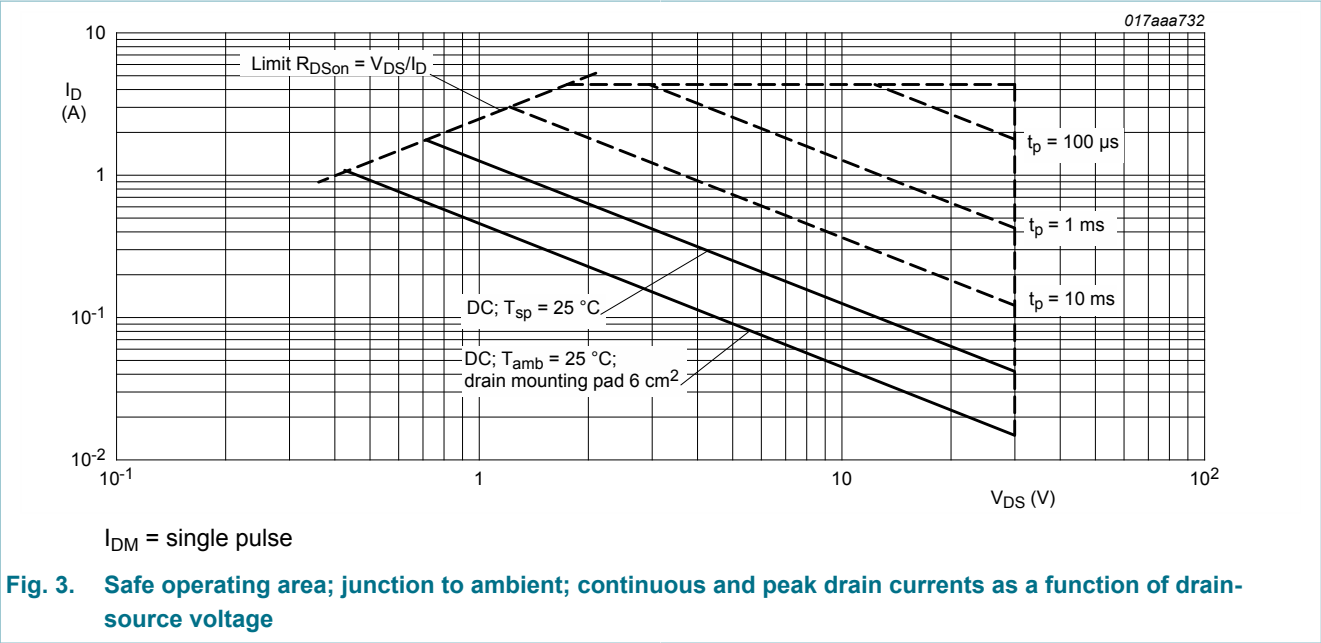
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$T_{amb} = 25\text{ }^{\circ}\text{C}$		-	30	V
V_{GS}	gate-source voltage			-12	12	V
I_D	drain current	$V_{GS} = 4.5\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}; t \leq 5\text{ s}$	[1]	-	1.2	A
		$V_{GS} = 4.5\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}$	[1]	-	1.1	A
		$V_{GS} = 4.5\text{ V}; T_{amb} = 100\text{ }^{\circ}\text{C}$	[1]	-	0.7	A
I_{DM}	peak drain current	$T_{amb} = 25\text{ }^{\circ}\text{C}$; single pulse; $t_p \leq 10\text{ }\mu\text{s}$		-	4.4	A
P_{tot}	total power dissipation	$T_{amb} = 25\text{ }^{\circ}\text{C}$	[2]	-	325	mW
			[1]	-	455	mW
		$T_{sp} = 25\text{ }^{\circ}\text{C}$		-	1275	mW

Symbol	Parameter	Conditions		Min	Max	Unit
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain diode						
I _S	source current	T _{amb} = 25 °C	[1]	-	0.7	A

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.





6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	333	385	K/W
			[2]	-	240	275	K/W
		in free air; $t \leq 5\text{ s}$	[2]	-	203	235	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	85	100	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm^2 .

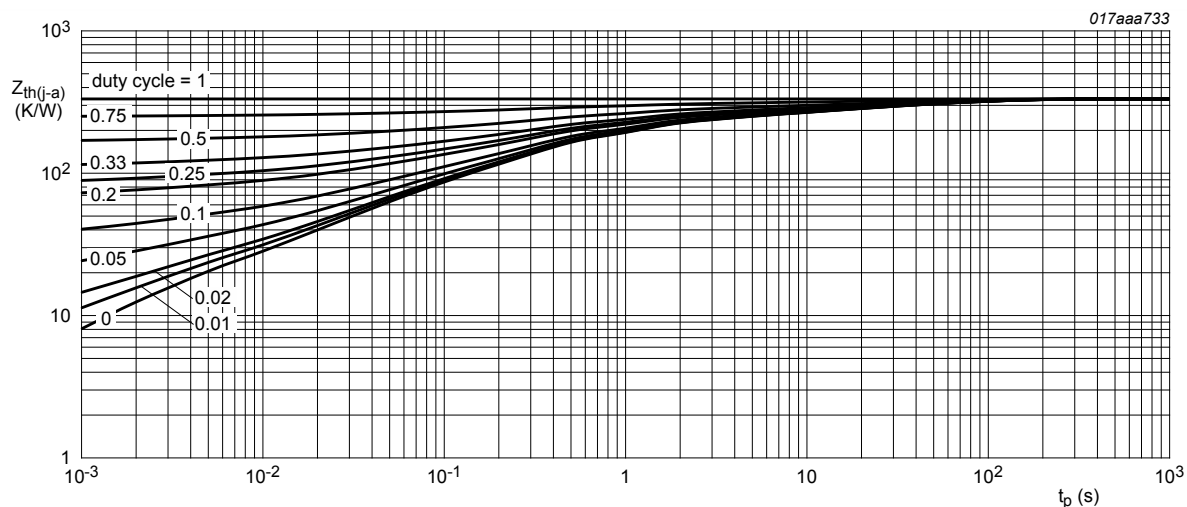


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

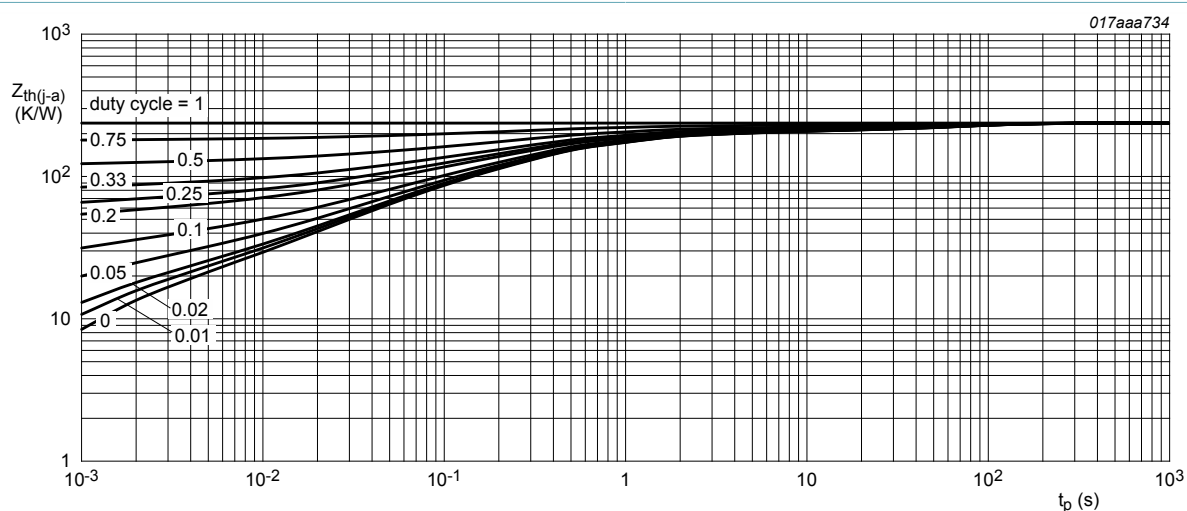


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A$; $V_{GS} = 0 V$; $T_j = 25 ^\circ C$	30	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A$; $V_{DS} = V_{GS}$; $T_j = 25 ^\circ C$	0.5	1	1.5	V
I_{DSS}	drain leakage current	$V_{DS} = 30 V$; $V_{GS} = 0 V$; $T_{amb} = 25 ^\circ C$	-	-	1	μA
		$V_{DS} = 30 V$; $V_{GS} = 0 V$; $T_{amb} = 150 ^\circ C$	-	-	10	μA

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
I _{GSS}	gate leakage current	V _{GS} = 12 V; V _{DS} = 0 V; T _j = 25 °C		-	-	100	nA
		V _{GS} = -12 V; V _{DS} = 0 V; T _j = 25 °C		-	-	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 1.1 A; T _j = 25 °C		-	185	250	mΩ
		V _{GS} = 4.5 V; I _D = 1.1 A; T _j = 150 °C		-	300	400	mΩ
		V _{GS} = 2.5 V; I _D = 0.25 A; T _j = 25 °C		-	255	365	mΩ
g _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 1.1 A; T _j = 25 °C		-	2.9	-	S
Dynamic characteristics							
Q _{G(tot)}	total gate charge	V _{DS} = 15 V; I _D = 1.1 A; V _{GS} = 4.5 V; T _j = 25 °C		-	0.87	1.3	nC
Q _{GS}	gate-source charge			-	0.17	-	nC
Q _{GD}	gate-drain charge			-	0.24	-	nC
C _{iss}	input capacitance	V _{DS} = 15 V; f = 1 MHz; V _{GS} = 0 V; T _j = 25 °C		-	76	-	pF
C _{oss}	output capacitance			-	30	-	pF
C _{rss}	reverse transfer capacitance			-	22	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 15 V; I _D = 1.1 A; V _{GS} = 4.5 V; R _{G(ext)} = 6 Ω; T _j = 25 °C		-	7	-	ns
t _r	rise time			-	11	-	ns
t _{d(off)}	turn-off delay time			-	16	-	ns
t _f	fall time			-	7	-	ns
Source-drain diode							
V _{SD}	source-drain voltage	I _S = 0.7 A; V _{GS} = 0 V; T _j = 25 °C		-	0.8	1.2	V

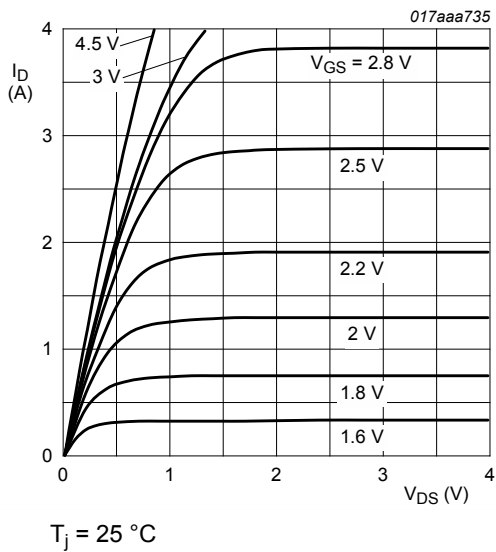


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

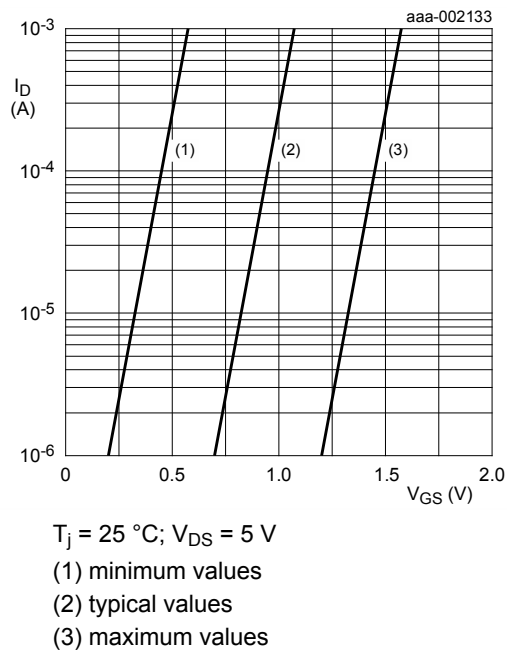


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

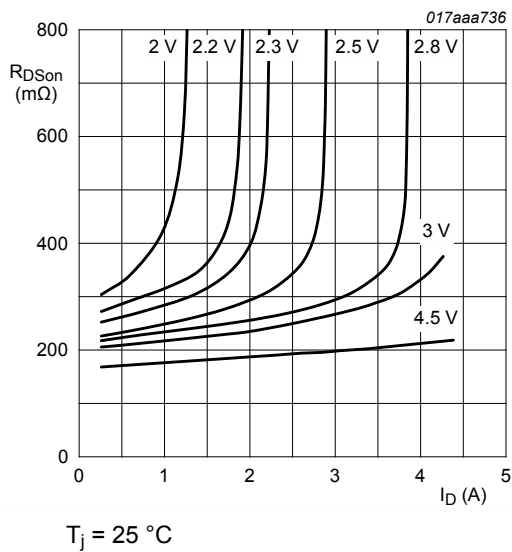


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

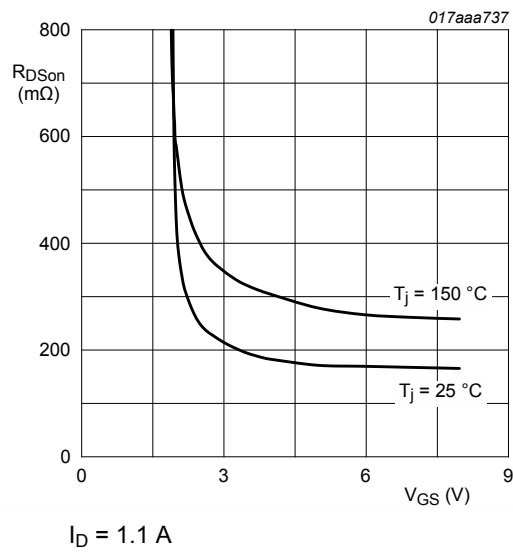


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

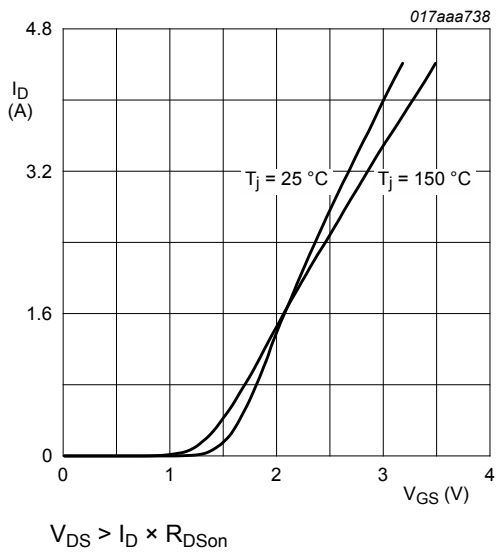


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

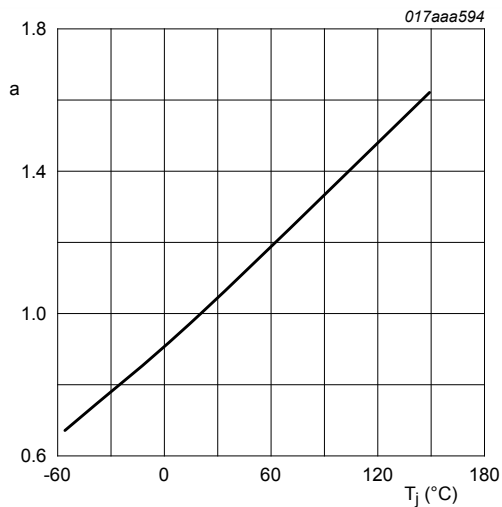


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}\text{C})}}$$

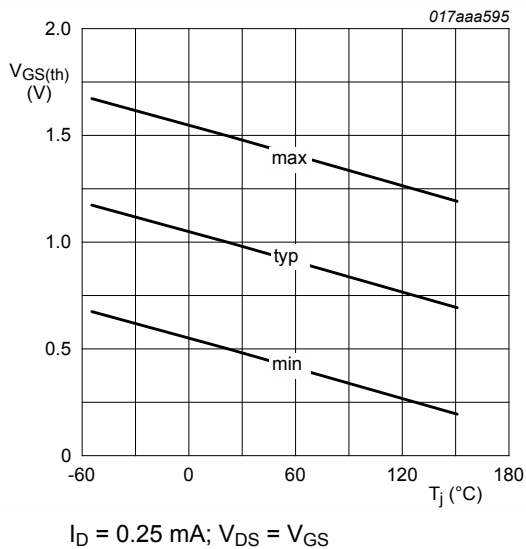


Fig. 12. Gate-source threshold voltage as a function of junction temperature

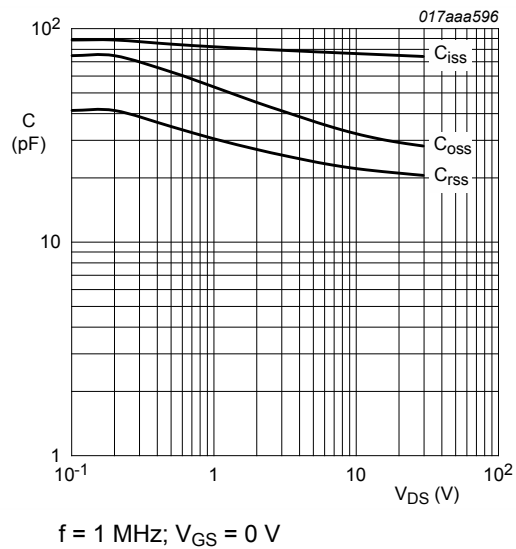


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

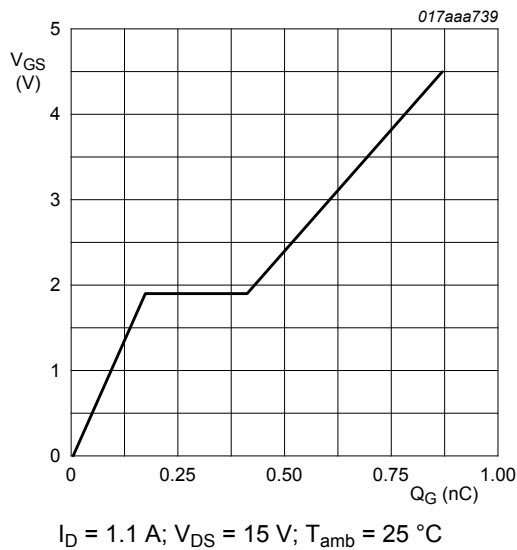


Fig. 14. Gate-source voltage as a function of gate charge; typical values

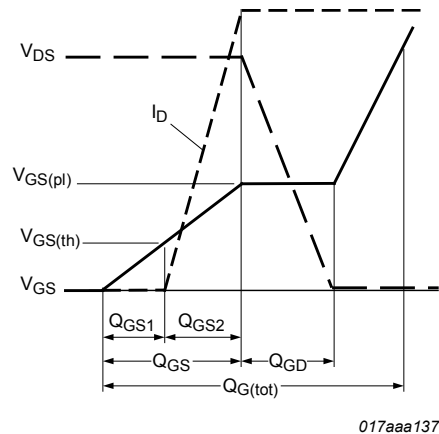


Fig. 15. Gate charge waveform definitions

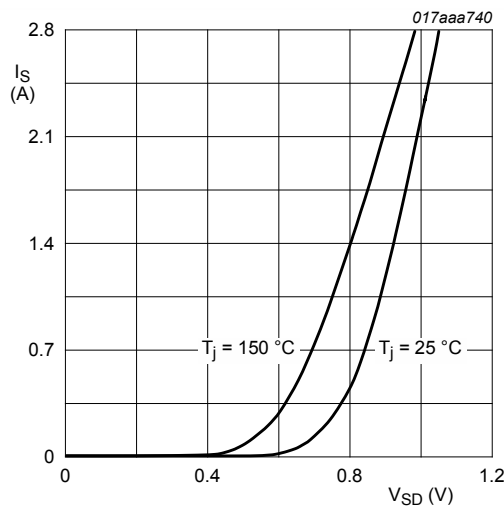


Fig. 16. Source current as a function of source-drain voltage; typical values

8. Test information

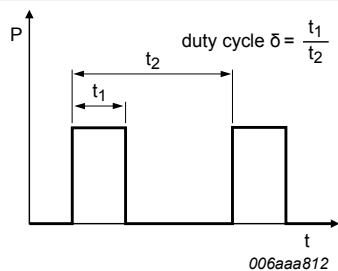
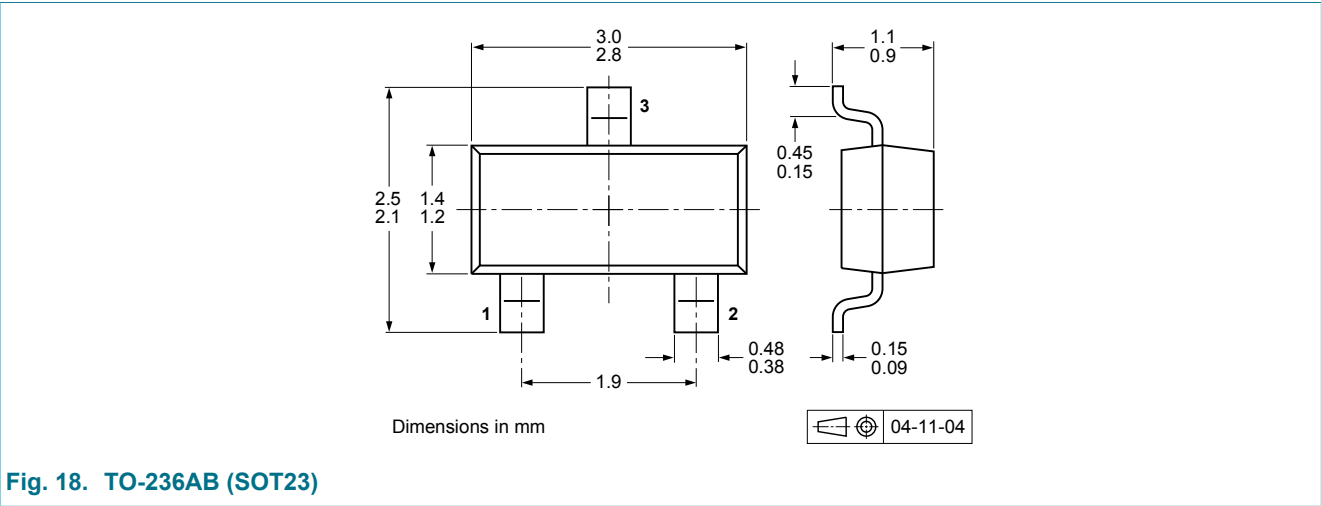
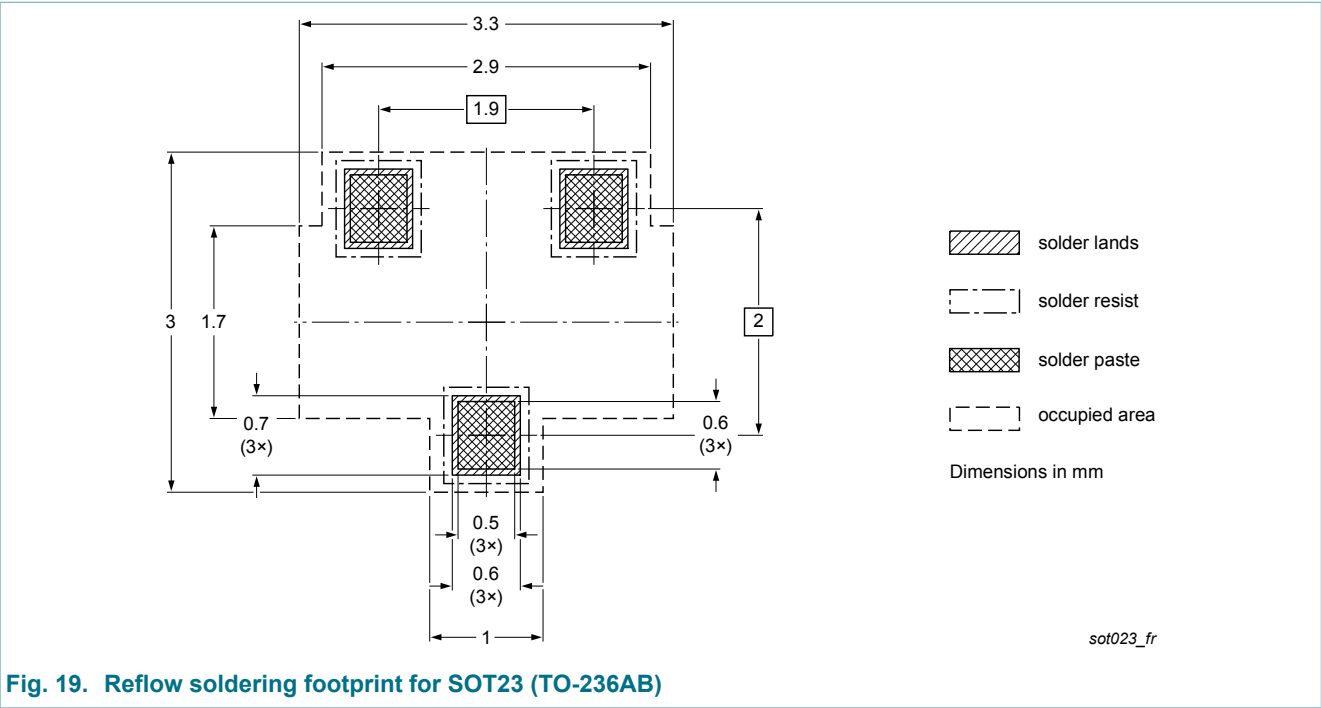


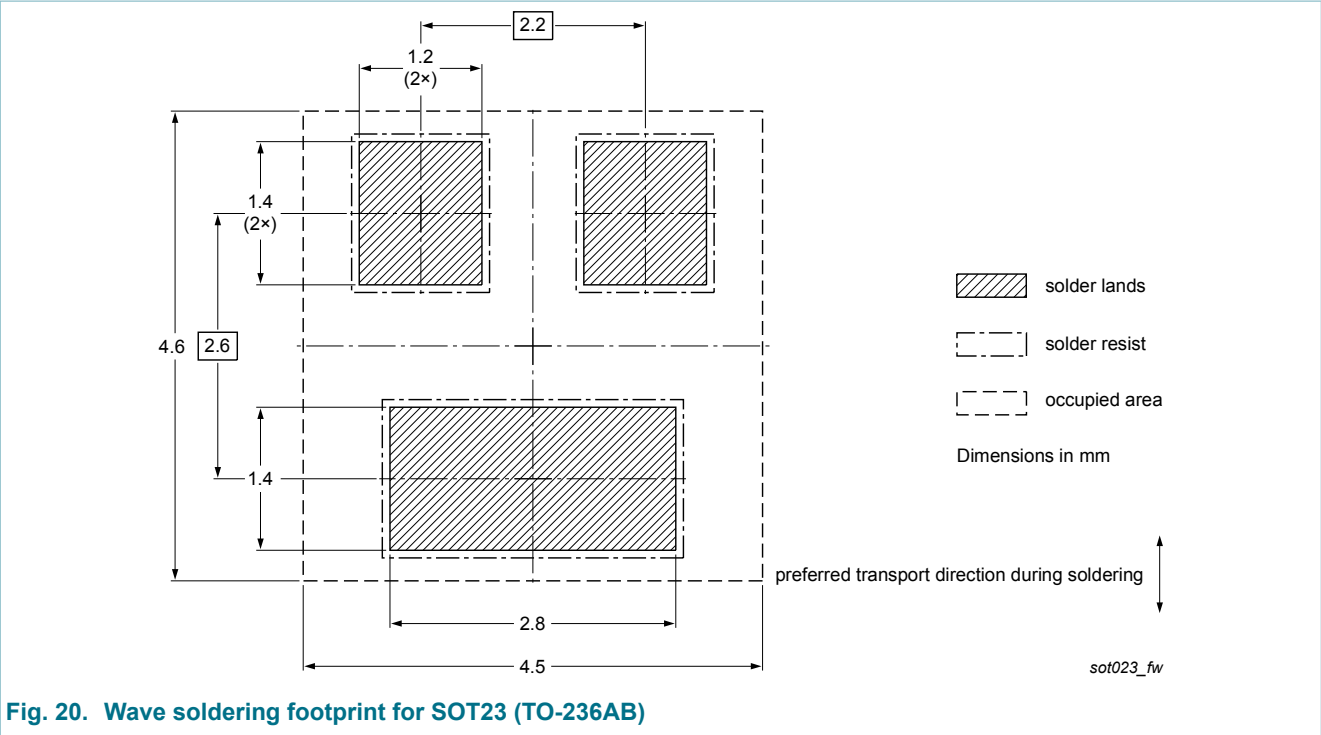
Fig. 17. Duty cycle definition

9. Package outline



10. Soldering





11. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV185XN v.1	20120803	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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